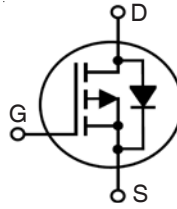


PolarP™ Power MOSFET

IXTR48P20P

P-Channel Enhancement Mode
Avalanche Rated

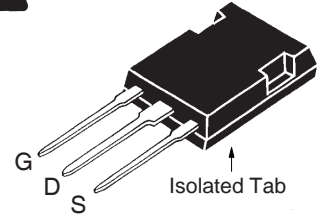


$$V_{DSS} = -200V$$

$$I_{D25} = -30A$$

$$R_{DS(on)} \leq 93m\Omega$$

ISOPLUS247
E153432



G = Gate D = Drain
S = Source

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	- 200	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	- 200	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ C$	- 30	A
I_{DM}	$T_C = 25^\circ C$, Pulse Width Limited by T_{JM}	-144	A
I_A	$T_C = 25^\circ C$	- 48	A
E_{AS}	$T_C = 25^\circ C$	2.5	J
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$	10	V/ns
P_D	$T_C = 25^\circ C$	190	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
T_{SOLD}	Plastic Body for 10s	260	$^\circ C$
V_{ISOL}	50/60 Hz, 1 Minute	2500	V~
F_C	Mounting Force	20..120/4.5..27	N/lb.
Weight		5	g

Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
 - UL Recognized Package
 - Isolated Mounting Surface
 - 2500V~ Electrical Isolation
- Avalanche Rated
- The Rugged PolarP™ Process
- Low Q_G
- Fast Intrinsic Diode
- Low Drain-to-Tab Capacitance
- Low Package Inductance

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- High-Side Switches
- Push-Pull Amplifiers
- DC Choppers
- Automatic Test Equipment
- Load-Switch Applications
- Fuel Injection Systems

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = -250\mu A$	- 200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	- 2.0		- 4.0 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$			- 25 μA - 200 μA
$R_{DS(on)}$	$V_{GS} = -10V$, $I_D = -24A$, Note 1			93 m Ω

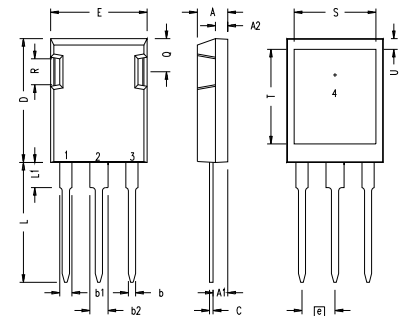
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = -10\text{V}$, $I_D = -24\text{A}$, Note 1	19	32	S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = -25\text{V}$, $f = 1\text{MHz}$		5400	pF
C_{oss}			1040	pF
C_{rss}			170	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = -10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = -24\text{A}$ $R_G = 3\Omega$ (External)		30	ns
t_r			46	ns
$t_{d(off)}$			67	ns
t_f			27	ns
$Q_{g(on)}$	$V_{GS} = -10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = -24\text{A}$		103	nC
Q_{gs}			23	nC
Q_{gd}			40	nC
R_{thJC}			0.66	$^\circ\text{C/W}$
R_{thCS}		0.15		$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_s	$V_{GS} = 0\text{V}$			- 48 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			-192 A
V_{SD}	$I_F = -24\text{A}$, $V_{GS} = 0\text{V}$, Note 1			- 3.3 V
t_{rr}	$I_F = -24\text{A}$, $-di/dt = -150\text{A}/\mu\text{s}$ $V_R = -100\text{V}$, $V_{GS} = 0\text{V}$		260	ns
Q_{RM}			4.2	μC
I_{RM}			- 32.2	A

Note 1: Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

ISOPLUS247 (IXTR) Outline



- 1 - Gate
- 2,4 - Drain
- 3 - Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.084	1.91	2.13
b2	.115	.123	2.92	3.12
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.520	.540	13.21	13.72
T	.620	.640	15.75	16.26
U	.065	.080	1.65	2.03

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

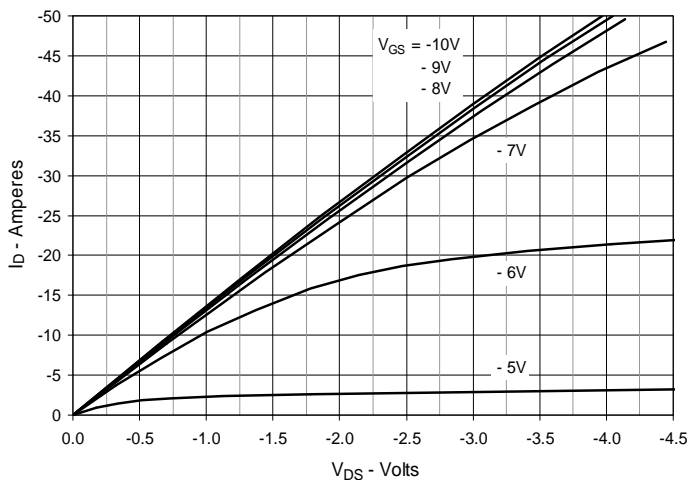


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

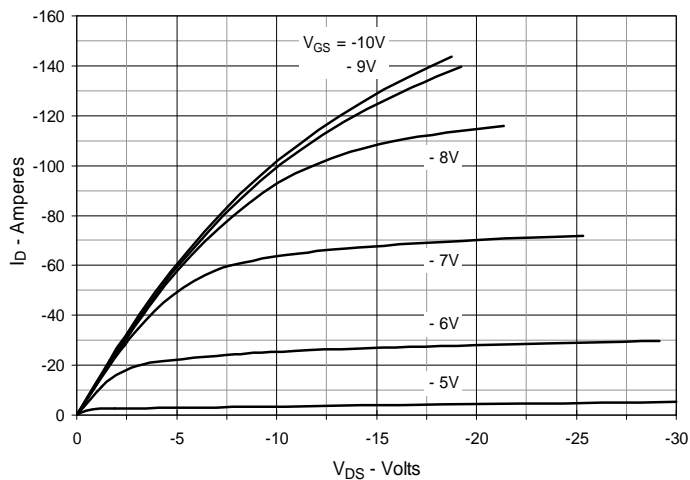


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

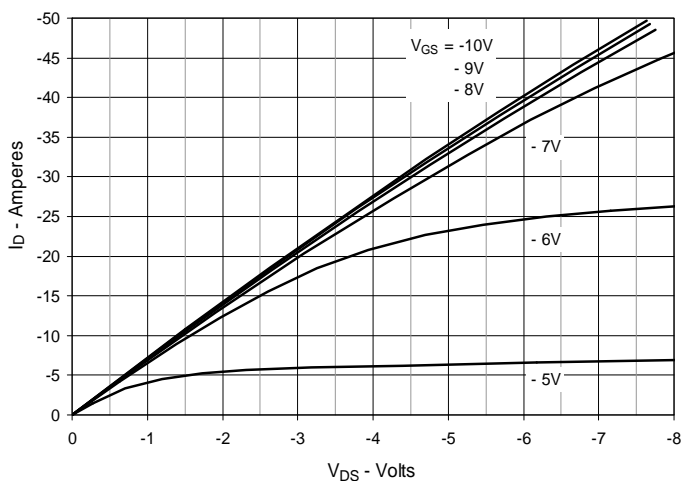


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = -24\text{A}$ Value vs. Junction Temperature

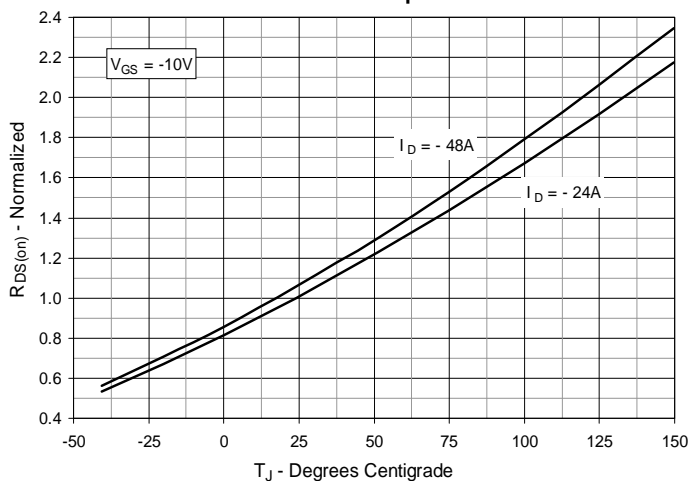


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = -24\text{A}$ Value vs. Drain Current

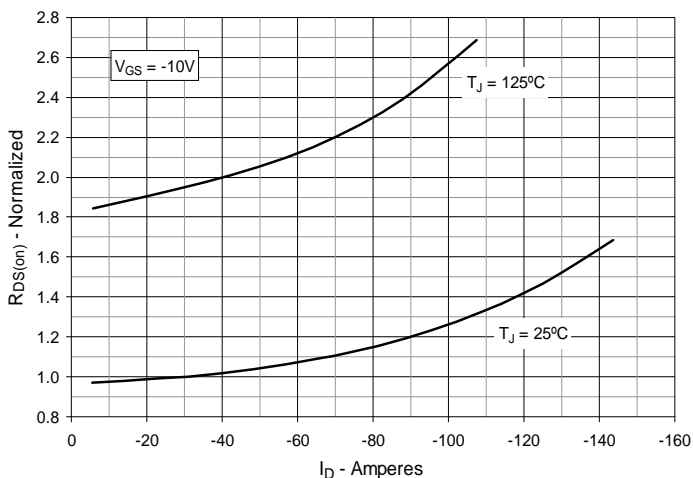


Fig. 6. Maximum Drain Current vs. Case Temperature

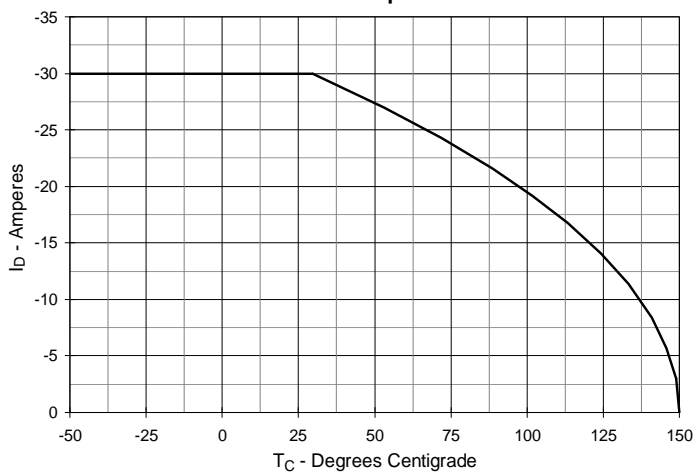


Fig. 7. Input Admittance

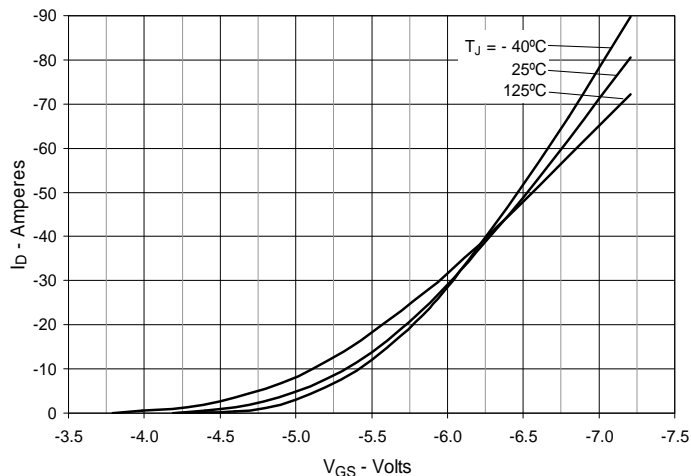


Fig. 8. Transconductance

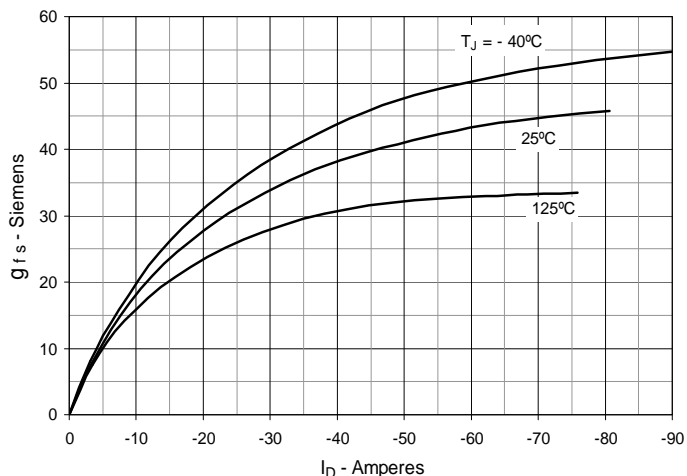


Fig. 9. Forward Voltage Drop of Intrinsic Diode

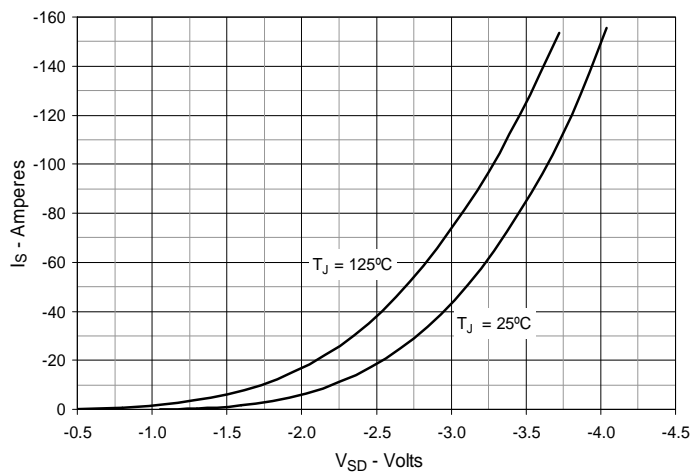


Fig. 10. Gate Charge

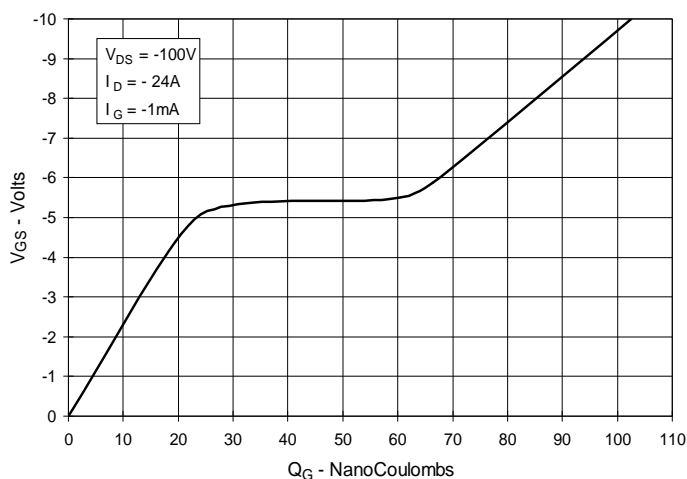


Fig. 11. Capacitance

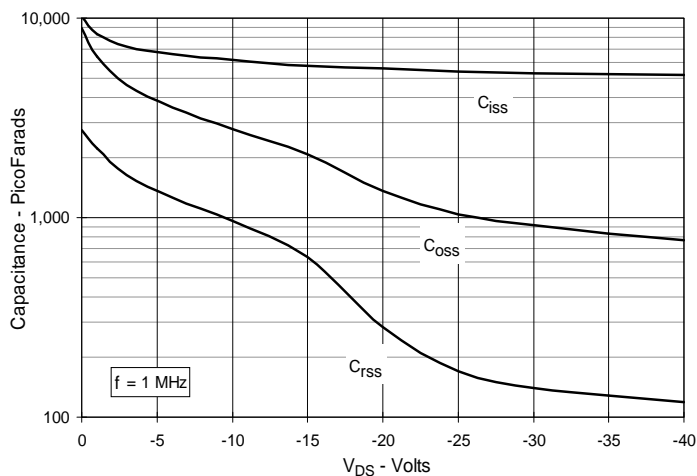


Fig. 12. Forward-Bias Safe Operating Area

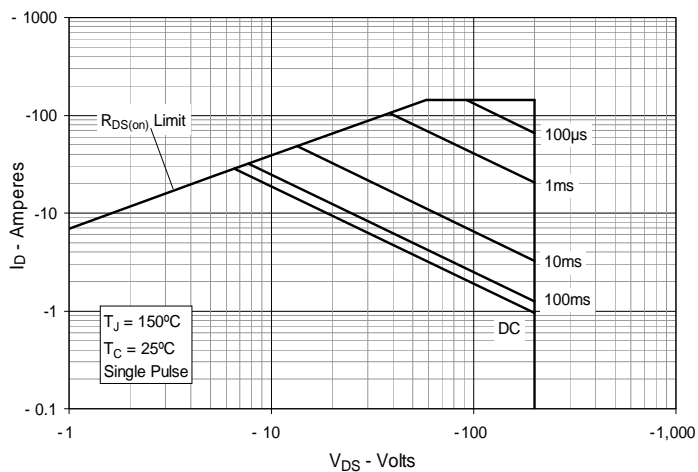


Fig. 13. Maximum Transient Thermal Impedance

